**GCA AS200 Autostep 5X i-line stepper**

<table>
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<tr>
<th>Instrument</th>
<th>Resist</th>
<th>Prebake</th>
<th>Exposure Time, PEB</th>
<th>Development</th>
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</thead>
<tbody>
<tr>
<td>AS200</td>
<td>OiR 620-7i</td>
<td>90°C, 60 sec.</td>
<td>0.16, 115°C, 60 sec.</td>
<td>300MIF, 60 sec.</td>
</tr>
<tr>
<td>AS200</td>
<td>OiR 897-12i</td>
<td>90°C, 60 sec.</td>
<td>0.2, 115°C, 90 sec.</td>
<td>300MIF, 60 sec.</td>
</tr>
<tr>
<td>AS200</td>
<td>SPR 700-1.2</td>
<td>95°C, 60 sec.</td>
<td>0.2, 115°C, 60 sec.</td>
<td>300MIF, 60 sec.</td>
</tr>
<tr>
<td>AS200</td>
<td>SPR 955CM-0.9</td>
<td>90°C, 90 sec.</td>
<td>0.17, 120°C, 90 sec.</td>
<td>300MIF, 60 sec.</td>
</tr>
<tr>
<td>AS200</td>
<td>SPR 955CM-2.1</td>
<td>90°C, 90 sec.</td>
<td>0.23, 120°C, 90 sec.</td>
<td>300MIF, 60 sec.</td>
</tr>
<tr>
<td>AS200</td>
<td>AZ P4903</td>
<td>115°C, 90 - 180 sec.</td>
<td>(wait 45 min.) 0.9</td>
<td>AZ 421K, 3 min.</td>
</tr>
</tbody>
</table>

**Note:** all exposure times are approximate. Your process may be 0.5 - 2x these values or more.

The AS200 stepper uses 365nm illumination. These resists are specified as i-line or broadband; g-line resists should not be used. Output is measured as around 200mW/cm² @365nm. Post exposure bake (PEB) is required for most of these processes.

**Image reversal:** expose as usual, run YES oven NH₃ process, flood expose 60 sec. using HTG, develop 60 sec. in MF321. Thicker films may require 300MIF or longer develop times.

Image reversal for these resists should be fully characterized in the usual way. Be sure to measure the resist thickness after development to make certain that full height is retained. Underexposure will result in thinner resist with poor sidewall profile.